

[THIN FILM TRANSISTOR AND FABRICATING METHOD THEREOF]

Abstract

A method for fabricating a thin film transistor (TFT) is described. A MoNb gate is formed on a substrate, and an insulating layer is formed on the substrate covering the gate. A channel layer is formed on the insulating layer above the gate, and a source/drain is formed on the channel layer to constitute a TFT. Since the gate is constituted of a MoNb layer, the contact resistance thereof can be reduced.